

REVISIONS

LTR	DESCRIPTION	DATE (YR-MO-DA)	APPROVED
A	Redrawn. Update paragraphs to MIL-PRF-38535 requirements. Remove class M requirements throughout. - drw	15-11-05	Charles F. Saffle



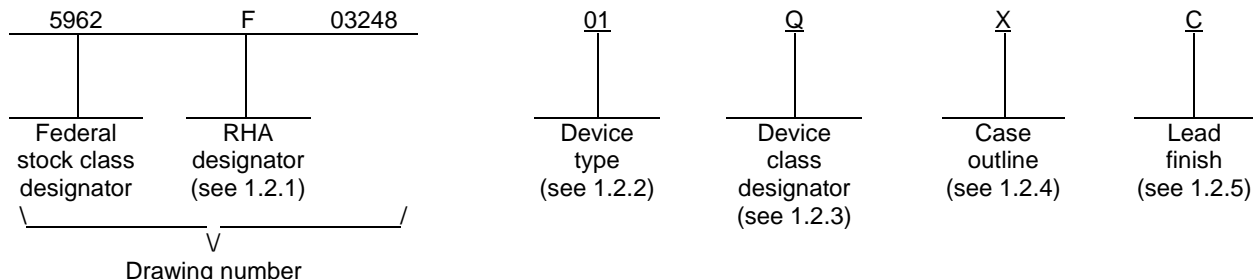
REV																			
SHEET																			
REV	A	A	A																
SHEET	15	16	17																
REV STATUS OF SHEETS	REV			A	A	A	A	A	A	A	A	A	A	A	A	A	A	A	
	SHEET			1	2	3	4	5	6	7	8	9	10	11	12	13	14		

PMIC N/A	PREPARED BY Rick Officer	<p align="center"><b>DLA LAND AND MARITIME</b>  <b>COLUMBUS, OHIO 43218-3990</b>  <a href="http://www.landandmaritime.dla.mil">http://www.landandmaritime.dla.mil</a></p>																
<p align="center"><b>STANDARD MICROCIRCUIT DRAWING</b></p> <p>THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS AND AGENCIES OF THE DEPARTMENT OF DEFENSE</p> <p align="center">AMSC N/A</p>	CHECKED BY Rajesh Pithadia																	
	APPROVED BY Raymond Monnin	<p align="center">MICROCIRCUIT, DIGITAL-LINEAR, RADIATION HARDENED, 9 AMP NON-INVERTING 5 V LOGIC UVLO FET DRIVER, MONOLITHIC SILICON</p>																
	DRAWING APPROVAL DATE 03-09-30																	
	REVISION LEVEL A	<table border="1"> <tr> <td>SIZE A</td> <td>CAGE CODE <b>67268</b></td> <td><b>5962-03248</b></td> </tr> </table>	SIZE A	CAGE CODE <b>67268</b>	<b>5962-03248</b>													
SIZE A	CAGE CODE <b>67268</b>	<b>5962-03248</b>																
		SHEET 1 OF 17																

1. SCOPE

1.1 Scope. This drawing documents two product assurance class levels consisting of high reliability (device class Q) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels is reflected in the PIN.

1.2 PIN. The PIN is as shown in the following example:



1.2.1 RHA designator. Device classes Q and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.

1.2.2 Device type. The device type identifies the circuit function as follows:

<u>Device type</u>	<u>Generic number</u>	<u>Circuit function</u>
01	ISL74422BRH	Radiation hardened, non-inverting 9 amp 5 V logic UVLO MOSFET driver

1.2.3 Device class designator. The device class designator is a single letter identifying the product assurance level as follows:

<u>Device class</u>	<u>Device requirements documentation</u>
Q or V	Certification and qualification to MIL-PRF-38535

1.2.4 Case outline. The case outline is as designated in MIL-STD-1835 as follows:

<u>Outline letter</u>	<u>Descriptive designator</u>	<u>Terminals</u>	<u>Package style</u>
X	CDFP4-F16	16	Flat pack

1.2.5 Lead finish. The lead finish is as specified in MIL-PRF-38535 for device classes Q and V.

<b>STANDARD MICROCIRCUIT DRAWING</b> DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE <b>A</b>		<b>5962-03248</b>
		REVISION LEVEL <b>A</b>	SHEET <b>2</b>

1.3 Absolute maximum ratings. 1/

Supply voltage (V <sub>S</sub> ) .....	20 V
Input voltage range (V <sub>IN</sub> ) .....	GND – 6.5 V to +V <sub>S</sub> +0.3 V 2/
DC input current, any one input (V <sub>IN</sub> ≤ V <sub>S</sub> +0.3 V or V <sub>IN</sub> ≥ GND – 6.5 V).....	10 mA
Output short circuit duration (single supply) .....	Continuous 3/
Maximum power dissipation (P <sub>D</sub> ) .....	625 mW
Maximum junction temperature (T <sub>J</sub> ) .....	175°C
Maximum storage temperature .....	-65°C to +150°C
Maximum lead temperature (soldering 10 seconds) .....	265°C
Thermal resistance, junction-to-case (θ <sub>JC</sub> ) .....	12°C/W
Thermal resistance, junction-to-ambient (θ <sub>JA</sub> ) .....	80°C/W 4/

1.4 Recommended operating conditions.

Supply voltage range (V <sub>S</sub> ) .....	8 V to 18 V
Under voltage lockout (UVLO) .....	< 6.0 V
Operating ambient temperature range .....	-55°C to +125°C

1.5 Radiation features.

Maximum total dose available: (dose rate = 50 - 300 rad(Si) / s)	
Device classes Q, and V .....	300 Krads (Si) 5/
Latch up immune .....	6/

2. APPLICABLE DOCUMENTS

2.1 Government specification, standards, and handbooks. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATION

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-883 - Test Method Standard Microcircuits.  
MIL-STD-1835 - Interface Standard Electronic Component Case Outlines.

DEPARTMENT OF DEFENSE HANDBOOKS

MIL-HDBK-103 - List of Standard Microcircuit Drawings.  
MIL-HDBK-780 - Standard Microcircuit Drawings.

(Copies of these documents are available online at <http://quicksearch.dla.mil> or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

- 1/ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.
- 2/ Inputs must not go more negative than GND – 6.5 V.
- 3/ Short circuit from the output to V<sub>S</sub> can cause excessive heating and eventual destruction.
- 4/ θ<sub>JA</sub> is measured with the component mounted on an evaluation PC board in free air.
- 5/ These parts may be dose rate sensitive in a space environment and may demonstrate enhanced low dose rate effects. Radiation end point limits for the noted parameters are guaranteed only for the conditions specified in MIL-STD-883, method 1019, condition A.
- 6/ Guaranteed by process or design.

<b>STANDARD MICROCIRCUIT DRAWING</b> DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE <b>A</b>		<b>5962-03248</b>
		REVISION LEVEL <b>A</b>	SHEET <b>3</b>

2.2 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

### 3. REQUIREMENTS

3.1 Item requirements. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 as specified herein, or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.

3.1.1 Microcircuit die. For the requirements for microcircuit die, see appendix A to this document.

3.2 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V.

3.2.1 Case outline. The case outline shall be in accordance with 1.2.4 herein.

3.2.2 Terminal connections. The terminal connections shall be as specified on figure 1.

3.2.3 Truth table. The truth table shall be as specified on figure 2.

3.2.4 Logic diagram. The logic diagram shall be as specified on figure 3.

3.2.5 Radiation exposure circuit. The radiation exposure circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing and acquiring activity upon request.

3.3 Electrical performance characteristics and postirradiation parameter limits. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full ambient operating temperature range.

3.4 Electrical test requirements. The electrical test requirements shall be the subgroups specified in table IIA. The electrical tests for each subgroup are defined in table I.

3.5 Marking. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535.

3.5.1 Certification/compliance mark. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535.

3.6 Certificate of compliance. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). The certificate of compliance submitted to DLA Land and Maritime-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein .

3.7 Certificate of conformance. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 shall be provided with each lot of microcircuits delivered to this drawing.

<b>STANDARD MICROCIRCUIT DRAWING</b> DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE <b>A</b>		<b>5962-03248</b>
		REVISION LEVEL A	SHEET 4

TABLE I. Electrical performance characteristics.

Test	Symbol	Conditions 1/ -55°C ≤ T <sub>A</sub> ≤ +125°C unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
Power supply current, low	I <sub>SSB</sub> low	V <sub>S</sub> = 18 V, V <sub>IN</sub> = 0.8 V	1, 2, 3	01		2.1	mA
		M, D, P, L, R, F 2/, 3/	1			2.1	
Power supply current, high	I <sub>SSB</sub> high	V <sub>S</sub> = 18 V, V <sub>IN</sub> = 10.0 V	1, 2, 3	01		2.7	mA
		M, D, P, L, R, F 2/, 3/	1			2.7	
Input current, low	I <sub>IL</sub>	V <sub>S</sub> = 18 V, V <sub>IN</sub> = 0 V	1, 2, 3	01	-10	+10	μA
		M, D, P, L, R, F 2/, 3/	1		-10	+10	
Input current, high	I <sub>IH</sub>	V <sub>S</sub> = 18 V, V <sub>IN</sub> = 18 V	1, 2, 3	01	-10	+10	μA
		M, D, P, L, R, F 2/, 3/	1		-10	+10	
Voltage output, low	V <sub>OL</sub>	V <sub>S</sub> = 18 V, I <sub>OUT</sub> = 10 mA	1, 2, 3	01		0.8	V
		M, D, P, L, R, F 2/, 3/	1			0.8	
Voltage output, high	V <sub>OH</sub>	V <sub>S</sub> = 18 V, I <sub>OUT</sub> = 10 mA	1, 2, 3	01	16.9		V
		M, D, P, L, R, F 2/, 3/	1		16.9		
Input voltage, low	V <sub>IL1</sub>	V <sub>S</sub> = 18 V, limits applied during functional test	1, 2, 3	01		0.8	V
			M, D, P, L, R, F 2/, 3/		1		
	V <sub>IL2</sub>	V <sub>S</sub> = 8 V, limits applied during functional test	1, 2, 3			0.8	
			M, D, P, L, R, F 2/, 3/		1		
Input voltage, high	V <sub>IH1</sub>	V <sub>S</sub> = 18 V, limits applied during functional test	1, 2	01	3.0		V
			3		3.5		
			M, D, P, L, R, F 2/, 3/		1	3.0	
	V <sub>IH2</sub>	V <sub>S</sub> = 8 V, limits applied during functional test	1, 2		3.0		
			3		3.5		
			M, D, P, L, R, F 2/, 3/		1	3.0	
Functional test	F <sub>T</sub>	V <sub>S</sub> = 8 V, V <sub>S</sub> = 18 V	7, 8A, 8B	01			
		M, D, P, L, R, F 2/, 3/	7, 8A, 8B				

See footnotes at end of table.

<b>STANDARD MICROCIRCUIT DRAWING</b> DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE <b>A</b>		<b>5962-03248</b>
		REVISION LEVEL A	SHEET 5

TABLE I. Electrical performance characteristics – continued.

Test	Symbol	Conditions <sup>1/</sup> -55°C ≤ T <sub>A</sub> ≤ +125°C unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
Output resistance, output high	RONH	V <sub>S</sub> = 18 V, V <sub>IN</sub> = 5.0 V, I <sub>OUT</sub> = 175 mA to 225 mA M,D,P,L,R,F <u>2/</u> , <u>3/</u>	1, 3	01		1.3	Ω
			2			1.5	
			1			1.3	
Output resistance, output low	RONL	V <sub>S</sub> = 18 V, V <sub>IN</sub> = 0.8 V, I <sub>OUT</sub> = 175 mA to 225 mA M,D,P,L,R,F <u>2/</u> , <u>3/</u>	1, 3	01		1.5	Ω
			2			1.7	
			1			1.5	
UVLO versus rising threshold		M,D,P,L,R,F <u>2/</u> , <u>3/</u>	1, 3	01	6.9	7.5	V
			2		6.6	7.2	
			1		6.9	7.5	
UVLO versus falling threshold hysteresis		M,D,P,L,R,F <u>2/</u> , <u>3/</u>	1, 3	01	6.3	6.9	V
			2		6.0	6.6	
			1		6.3	6.9	
UVLO hysteresis (rising – falling)		M,D,P,L,R,F <u>2/</u> , <u>3/</u>	1, 2, 3	01	0.3		V
			1		0.3		
Propagation delay, low	t <sub>PHL</sub>	V <sub>S</sub> = 18 V, C <sub>L</sub> = 10 nF M,D,P,L,R,F <u>2/</u> , <u>3/</u>	9, 11	01		140	ns
			10			175	
			9			140	
Propagation delay, high	t <sub>PLH</sub>	V <sub>S</sub> = 18 V, C <sub>L</sub> = 10 nF M,D,P,L,R,F <u>2/</u> , <u>3/</u>	9, 11	01		140	ns
			10			175	
			9			140	
Response time, fall	TF	V <sub>S</sub> = 15 V, C <sub>L</sub> = 10 nF M,D,P,L,R,F <u>2/</u> , <u>3/</u>	9, 11	01		125	ns
			10			135	
			9			125	

See footnotes at end of table.

<b>STANDARD MICROCIRCUIT DRAWING</b> DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE <b>A</b>		<b>5962-03248</b>
		REVISION LEVEL <b>A</b>	SHEET <b>6</b>

TABLE I. Electrical performance characteristics – continued.

Test	Symbol	Conditions <u>1/</u> -55°C ≤ T <sub>A</sub> ≤ +125°C unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
Response time, rise	TR	V <sub>S</sub> = 15 V, C <sub>L</sub> = 10 nF	9, 11	01		125	ns
			10			135	
			M,D,P,L,R,F <u>2/</u> , <u>3/</u>		9		

1/ V<sub>S</sub> = as specified.

2/ The devices supplied to this drawing meet all levels M, D, P, L, R, F of irradiation (classes Q, and V). However, this device is only tested at the "F" level (classes Q, and V). Pre and Post irradiation values are identical unless otherwise specified in Table I. When performing post irradiation electrical measurements for any RHA level, T<sub>A</sub> = +25°C.

3/ These parts may be dose rate sensitive in a space environment and may demonstrate enhanced low dose rate effects. Radiation end point limits for the noted parameters are guaranteed only for the conditions specified in MIL-STD-883, method 1019, condition A.

<b>STANDARD MICROCIRCUIT DRAWING</b> DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE <b>A</b>		<b>5962-03248</b>
		REVISION LEVEL <b>A</b>	SHEET <b>7</b>

Device type	01
Case outline	X
Terminal number	Terminal symbol
1	NC
2	NC
3	$V_S$ (LOGIC INPUT BUFFER (IB)) <u>1/</u>
4	$V_{IN}$
5	GND (LOGIC RTN INPUT BUFFER (IB)) <u>2/</u>
6	NC
7	NC
8	GND (OUTPUT BUFFER (OB)) <u>3/</u>
9	GND (OUTPUT BUFFER (OB)) <u>3/</u>
10	NC
11	NC
12	$-V_{OUT}$ <u>4/</u>
13	$+V_{OUT}$ <u>4/</u>
14	NC
15	$V_S$ (OUTPUT BUFFER (OB)) <u>5/</u>
16	$V_S$ (OUTPUT BUFFER (OB)) <u>5/</u>

- 1/  $V_S$  (LOGIC INPUT BUFFER) pin 3 provides the supply voltage for the control logic. It is not internally connected to pins 15 and 16 for noise immunity purposes, but it must be connected externally.
- 2/ GND (LOGIC RTN INPUT BUFFER) pin 5 is the control logic return. It is not internally connected to pins 8 and 9 for noise immunity purposes, but it must be connected externally.
- 3/ GND (OUTPUT BUFFER) pins 8 and 9 must be connected to GND.
- 4/  $V_{OUT}$  pins 12 and 13 must be externally connected.
- 5/  $V_S$  (OUTPUT BUFFER) pins 15 and 16 must be connected to  $V_S$ .

FIGURE 1. Terminal connections.

INPUT	OUTPUT
1	1
0	0

FIGURE 2. Truth table.

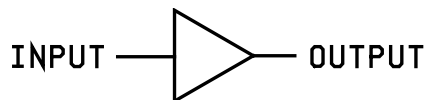


FIGURE 3. Logic diagram.

<b>STANDARD MICROCIRCUIT DRAWING</b> DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE <b>A</b>		<b>5962-03248</b>
		REVISION LEVEL <b>A</b>	SHEET <b>8</b>



4. VERIFICATION

4.1 Sampling and inspection. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.

4.2 Screening. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection.

4.2.1 Additional criteria for device classes Q and V.

- a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015 of MIL-STD-883.
- b. Interim and final electrical test parameters shall be as specified in table IIA herein.
- c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.

4.3 Qualification inspection for device classes Q and V. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4 Conformance inspection. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections, and as specified herein.

4.4.1 Group A inspection.

- a. Tests shall be as specified in table IIA herein.
- b. Subgroups 4, 5, and 6 in table I, method 5005 of MIL-STD-883 shall be omitted.
- c. For device classes Q and V, subgroups 7 and 8 shall include verifying the functionality of the device.

<b>STANDARD MICROCIRCUIT DRAWING</b> DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE <b>A</b>		<b>5962-03248</b>
		REVISION LEVEL <b>A</b>	SHEET <b>9</b>

TABLE IIA. Electrical test requirements.

Test requirements	Subgroups (in accordance with MIL-PRF-38535, table III)	
	Device class Q	Device class V
Interim electrical parameters (see 4.2)	1, 7	1, 7
Final electrical parameters (see 4.2)	1, 2, 3, 7, 8A, 8B, 9, 10, 11 <u>1/</u>	1, 2, 3, 7, 8A, 8B, 9, 10, 11 <u>2/</u> , <u>3/</u>
Group A test requirements (see 4.4)	1, 2, 3, 7, 8A, 8B, 9, 10, 11	1, 2, 3, 7, 8A, 8B, 9, 10, 11
Group C end-point electrical parameters (see 4.4)	1, 2, 3, 7, 8A, 8B, 9, 10, 11	1, 2, 3, 7, 8A, 8B, 9, 10, 11 <u>3/</u>
Group D end-point electrical parameters (see 4.4)	1, 7, 9	1, 7, 9
Group E end-point electrical parameters (see 4.4)	1, 7, 9	1, 7, 9

1/ PDA applies to subgroup 1.

2/ PDA applies to subgroups 1, 7, and Δ's.

3/ Delta limits (see table IIB herein) shall be required and the delta values shall be computed with reference to the zero hour electrical parameters (see table I herein).

TABLE IIB. Burn-in and life test delta parameters. T<sub>A</sub> = +25°C

Parameters	Symbol	Min	Max	Unit
Power supply current, low	I <sub>SSB</sub> low		200	μA
Power supply current, high	I <sub>SSB</sub> high		200	μA
Input current, low	I <sub>IL</sub>		1	μA
Input current, high	I <sub>IH</sub>		1	μA

4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table IIA herein.

4.4.2.1 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.

4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table IIA herein.

<b>STANDARD MICROCIRCUIT DRAWING</b> DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE <b>A</b>		<b>5962-03248</b>
		REVISION LEVEL <b>A</b>	SHEET <b>10</b>

4.4.4 Group E inspection. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein). RHA levels for device classes M, Q and V shall be as specified in MIL-PRF-38535 and the end-point electrical parameters shall be as specified in table IIA herein. The end-point electrical parameters shall be as specified in table I group A subgroups or as modified in the QM plan.

4.4.4.1 Total dose irradiation testing. Total dose irradiation testing shall be performed in accordance with MIL-STD-883 method 1019, condition A and as specified herein.

4.4.4.1.1 Accelerated annealing test. Accelerated annealing tests shall be performed on all devices requiring a RHA level greater than 5k rads(Si). The post-anneal end-point electrical parameter limits shall be as specified in table I herein and shall be the pre-irradiation end-point electrical parameter limit at 25°C ±5°C. Testing shall be performed at initial qualification and after any design or process changes which may affect the RHA response of the device.

5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V.

6. NOTES

6.1 Intended use. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.

6.1.1 Replaceability. Microcircuits covered by this drawing will replace the same generic device covered by a contractor prepared specification or drawing.

6.2 Configuration control of SMD's. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished using DD Form 1692, Engineering Change Proposal.

6.3 Record of users. Military and industrial users should inform DLA Land and Maritime when a system application requires configuration control and which SMD's are applicable to that system. DLA Land and Maritime will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DLA Land and Maritime-VA, telephone (614) 692-8108.

6.4 Comments. Comments on this drawing should be directed to DLA Land and Maritime-VA, Columbus, Ohio 43218-3990, or telephone (614) 692-0540.

6.5 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.

6.6 Sources of supply.

6.6.1 Sources of supply for device classes Q and V. Sources of supply for device classes Q and V are listed in MIL-HDBK-103 and QML-38535. The vendors listed in MIL-HDBK-103 and QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DLA Land and Maritime-VA and have agreed to this drawing.

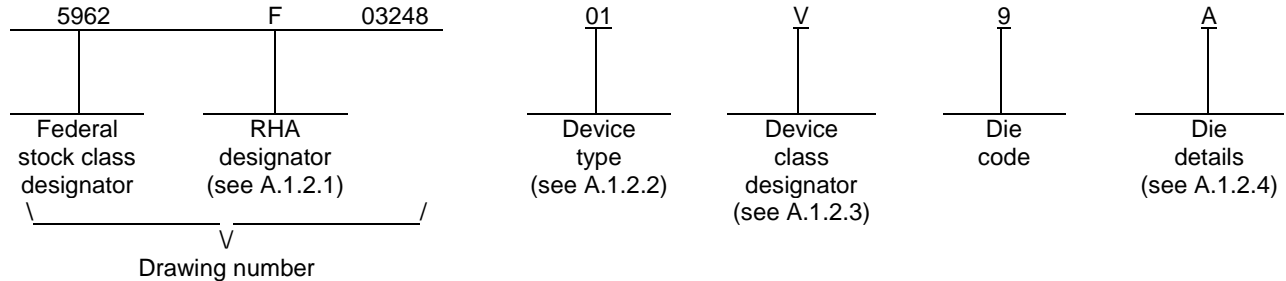
<b>STANDARD MICROCIRCUIT DRAWING</b> DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE <b>A</b>		<b>5962-03248</b>
		REVISION LEVEL <b>A</b>	SHEET <b>11</b>

APPENDIX A  
APPENDIX A FORMS A PART OF SMD 5962-03248

A.1 SCOPE

A.1.1 Scope. This appendix establishes minimum requirements for microcircuit die to be supplied under the Qualified Manufacturers List (QML) Program. QML microcircuit die meeting the requirements of MIL-PRF-38535 and the manufacturers approved QM plan for use in monolithic microcircuits, multi-chip modules (MCMs), hybrids, electronic modules, or devices using chip and wire designs in accordance with MIL-PRF-38534 are specified herein. Two product assurance classes consisting of military high reliability (device class Q) and space application (device class V) are reflected in the Part or Identification Number (PIN). When available, a choice of Radiation Hardiness Assurance (RHA) levels are reflected in the PIN.

A.1.2 PIN. The PIN is as shown in the following example:



A.1.2.1 RHA designator. Device classes Q and V RHA identified die meet the MIL-PRF-38535 specified RHA levels. A dash (-) indicates a non-RHA die.

A.1.2.2 Device type. The device type identifies the circuit function as follows:

<u>Device type</u>	<u>Generic number</u>	<u>Circuit function</u>
01	ISL74422BRH	Radiation hardened non-inverting 9 amp 5 V logic UVLO MOSFET driver

A.1.2.3 Device class designator.

<u>Device class</u>	<u>Device requirements documentation</u>
Q or V	Certification and qualification to the die requirements of MIL-PRF-38535

<b>STANDARD MICROCIRCUIT DRAWING</b> DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE <b>A</b>		<b>5962-03248</b>
		REVISION LEVEL <b>A</b>	SHEET <b>12</b>

APPENDIX A  
APPENDIX A FORMS A PART OF SMD 5962-03248

A.1.2.4 Die details. The die details designation is a unique letter which designates the die's physical dimensions, bonding pad locations and related electrical functions, interface materials, and other assembly related information, for each product and variant supplied to this appendix.

A.1.2.4.1 Die physical dimensions.

<u>Die type</u>	<u>Figure number</u>
01	A-1

A.1.2.4.2 Die bonding pad locations and electrical functions.

<u>Die type</u>	<u>Figure number</u>
01	A-1

A.1.2.4.3 Interface materials.

<u>Die type</u>	<u>Figure number</u>
01	A-1

A.1.2.4.4 Assembly related information.

<u>Die type</u>	<u>Figure number</u>
01	A-1

A.1.3 Absolute maximum ratings. See paragraph 1.3 herein for details.

A.1.4 Recommended operating conditions. See paragraph 1.4 herein for details.

<b>STANDARD MICROCIRCUIT DRAWING</b> DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE <b>A</b>		<b>5962-03248</b>
		REVISION LEVEL A	SHEET 13

APPENDIX A  
APPENDIX A FORMS A PART OF SMD 5962-03248

A.2 APPLICABLE DOCUMENTS.

A.2.1 Government specification, standards, and handbooks. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATION

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARD

MIL-STD-883 - Test Method Standard Microcircuits.

DEPARTMENT OF DEFENSE HANDBOOKS

MIL-HDBK-103 - List of Standard Microcircuit Drawings.

MIL-HDBK-780 - Standard Microcircuit Drawings.

(Copies of these documents are available online at <http://quicksearch.dla.mil> or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

A.2.2 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

A.3 REQUIREMENTS

A.3.1 Item requirements. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.

A.3.2 Design, construction and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein and the manufacturer's QM plan for device classes Q and V.

A.3.2.1 Die physical dimensions. The die physical dimensions shall be as specified in A.1.2.4.1 and on figure A-1.

A.3.2.2 Die bonding pad locations and electrical functions. The die bonding pad locations and electrical functions shall be as specified in A.1.2.4.2 and on figure A-1.

A.3.2.3 Interface materials. The interface materials for the die shall be as specified in A.1.2.4.3 and on figure A-1.

A.3.2.4 Assembly related information. The assembly related information shall be as specified in A.1.2.4.4 and on figure A-1.

A.3.2.5 Truth table. The truth table shall be as defined in paragraph 3.2.3 herein.

A.3.2.6 Logic diagram. The logic diagram shall be as defined in paragraph 3.2.4 herein.

A.3.2.7 Radiation exposure circuit. The radiation exposure circuit shall be as defined in paragraph 3.2.5 herein.

<b>STANDARD MICROCIRCUIT DRAWING</b> DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE <b>A</b>		<b>5962-03248</b>
		REVISION LEVEL <b>A</b>	SHEET <b>14</b>

APPENDIX A  
APPENDIX A FORMS A PART OF SMD 5962-03248

A.3.3 Electrical performance characteristics and post-irradiation parameter limits. Unless otherwise specified herein, the electrical performance characteristics and post-irradiation parameter limits are as specified in table I of the body of this document.

A.3.4 Electrical test requirements. The wafer probe test requirements shall include functional and parametric testing sufficient to make the packaged die capable of meeting the electrical performance requirements in table I.

A.3.5 Marking. As a minimum, each unique lot of die, loaded in single or multiple stack of carriers, for shipment to a customer, shall be identified with the wafer lot number, the certification mark, the manufacturer's identification and the PIN listed in A.1.2 herein. The certification mark shall be a "QML" or "Q" as required by MIL-PRF-38535.

A.3.6 Certification of compliance. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see A.6.4 herein). The certificate of compliance submitted to DLA Land and Maritime -VA prior to listing as an approved source of supply for this appendix shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and the requirements herein.

A.3.7 Certificate of conformance. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 shall be provided with each lot of microcircuit die delivered to this drawing.

A.4 VERIFICATION

A.4.1 Sampling and inspection. For device classes Q and V, die sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modifications in the QM plan shall not affect the form, fit, or function as described herein.

A.4.2 Screening. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and as defined in the manufacturer's QM plan. As a minimum, it shall consist of:

- a. Wafer lot acceptance for class V product using the criteria defined in MIL-STD-883, method 5007.
- b. 100% wafer probe (see paragraph A.3.4 herein).
- c. 100% internal visual inspection to the applicable class Q or V criteria defined in MIL-STD-883, method 2010 or the alternate procedures allowed in MIL-STD-883, method 5004.

A.4.3 Conformance inspection.

A.4.3.1 Group E inspection. Group E inspection is required only for parts intended to be identified as radiation assured (see A.3.5 herein). RHA levels for device classes Q and V shall be as specified in MIL-PRF-38535. End point electrical testing of packaged die shall be as specified in table IIA herein. Group E tests and conditions are as specified in paragraphs 4.4.4, 4.4.4.1 and 4.4.4.1.1 herein.

A.5 DIE CARRIER

A.5.1 Die carrier requirements. The requirements for the die carrier shall be accordance with the manufacturer's QM plan or as specified in the purchase order by the acquiring activity. The die carrier shall provide adequate physical, mechanical and electrostatic protection.

<b>STANDARD MICROCIRCUIT DRAWING</b> DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE <b>A</b>		<b>5962-03248</b>
		REVISION LEVEL <b>A</b>	SHEET <b>15</b>

APPENDIX A  
APPENDIX A FORMS A PART OF SMD 5962-03248

A.6 NOTES

A.6.1 Intended use. Microcircuit die conforming to this drawing are intended for use in microcircuits built in accordance with MIL-PRF-38535 or MIL-PRF-38534 for government microcircuit applications (original equipment), design applications, and logistics purposes.

A.6.2 Comments. Comments on this appendix should be directed to DLA Land and Maritime -VA, Columbus, Ohio, 43218-3990 or telephone (614)-692-0540.

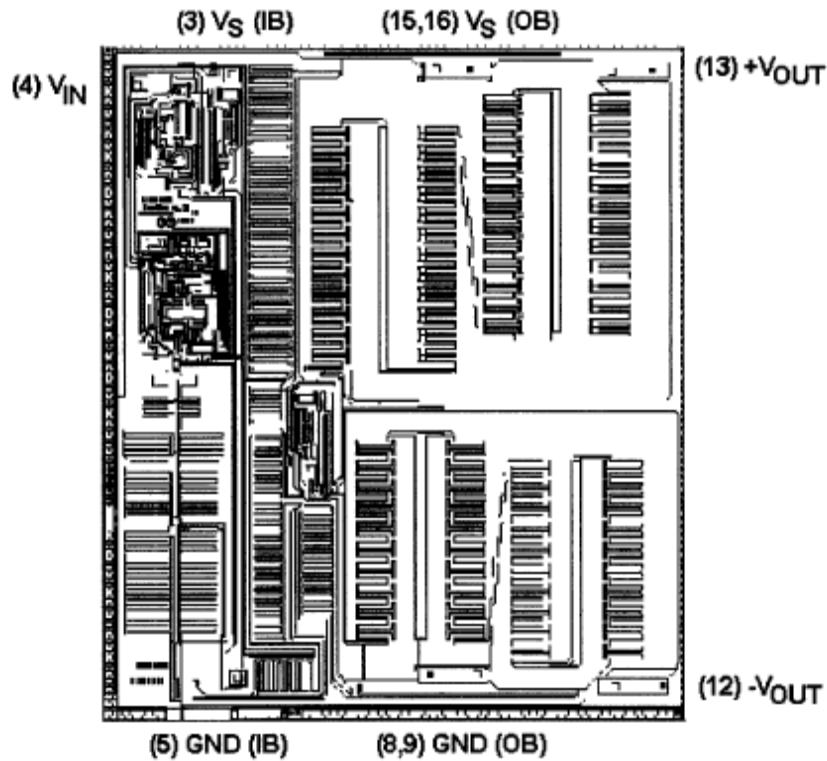
A.6.3 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.

A.6.4 Sources of supply for device classes Q and V. Sources of supply for device classes Q and V are listed in MIL-HDBK-103 and QML-38535. The vendors listed within MIL-HDBK-103 and QML-38535 have submitted a certificate of compliance (see A.3.6 herein) to DLA Land and Maritime -VA and have agreed to this drawing.

<b>STANDARD MICROCIRCUIT DRAWING</b> DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE <b>A</b>		<b>5962-03248</b>
		REVISION LEVEL <b>A</b>	SHEET <b>16</b>



APPENDIX A  
 APPENDIX A FORMS A PART OF SMD 5962-03248



Die bonding pad locations and electrical functions

Die physical dimensions.

Die size: 4191 microns x 4826 microns  
 Die thickness:  $19 \pm 1$  mils

Interface materials.

Top metallization: Al Si Cu  $16.0 \text{ k\AA} \pm 2 \text{ k\AA}$   
 Backside metallization: None

Glassivation.

Type: PSG  
 Thickness:  $8.0 \text{ k\AA} \pm 1.0 \text{ k\AA}$

Substrate: DI (dielectric isolation)

Assembly related information.

Substrate potential: Unbiased  
 Special assembly instructions: See figure 1 terminal connections.

FIGURE A-1. Die bonding pad locations and electrical functions.

<b>STANDARD          MICROCIRCUIT DRAWING</b> DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE <b>A</b>		<b>5962-03248</b>
		REVISION LEVEL A	SHEET 17

STANDARD MICROCIRCUIT DRAWING BULLETIN

DATE: 15-11-05

Approved sources of supply for SMD 5962-03248 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DLA Land and Maritime-VA. This information bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535. DLA Land and Maritime maintains an online database of all current sources of supply at <http://www.landandmaritime.dla.mil/Programs/Smcr/>.

Standard microcircuit drawing PIN <u>1/</u>	Vendor CAGE number	Vendor similar PIN <u>2/</u>
5962F0324801QXC	34371	ISL74422BRHQF
5962F0324801VXC	34371	ISL74422BRHVF
5962F0324801V9A	34371	ISL74422BRHVX

1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the vendor to determine its availability.

2/ Caution. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

Vendor CAGE  
number

34371

Vendor name  
and address

Intersil Corporation  
1650 Robert J. Conlan Blvd. NE  
Palm Bay, FL 32905-3406

The information contained herein is disseminated for convenience only and the Government assumes no liability whatsoever for any inaccuracies in the information bulletin.